Jul-2025

5 Ø

Q220 .> / / x N ?œ 3 « | o

NCHANNEL ENHANCEMENT MODE POWER MOSFET TO-220 Package

/ “

V_{DS} ()V= 200V I $_D$ =67A (V_{GS} = f 20)V

8*9 54& < S S : _ V S S

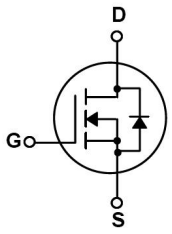
8*9 54& < S S : _ V S S

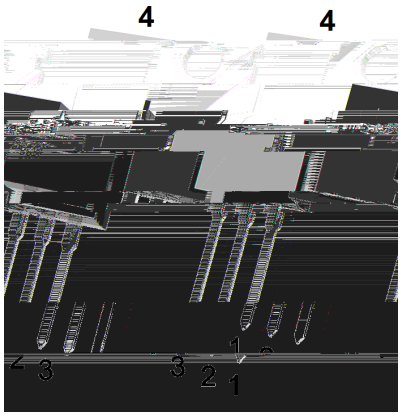
)í D }o HF Ø

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DC - DC C





PIN y G PIN 2 o 4 y D PIN 3 y S

, M V

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@	Z		% y
Dr Vo	DS	200	V
Dr Cr	ID(@TC=25)	67	A
	ID(@TC=100)	42	A
Pu Dr Cr *	IDM	175	A
Ga Vo	GS	f 20	V
Si Pu Av Ey (VDD=50V,L=1.0mH)	EAS	685	mJ
Cr Fr Cr	IS	67	A
Ma Po Di	PD(@TC=25)	227	W
Op Ju Te Ra	TJ, Tst	-55 to 150	
Th Re Ju to Am **	R JA	42	- /W
Th Re Ju to Ca	R JC	0.55	

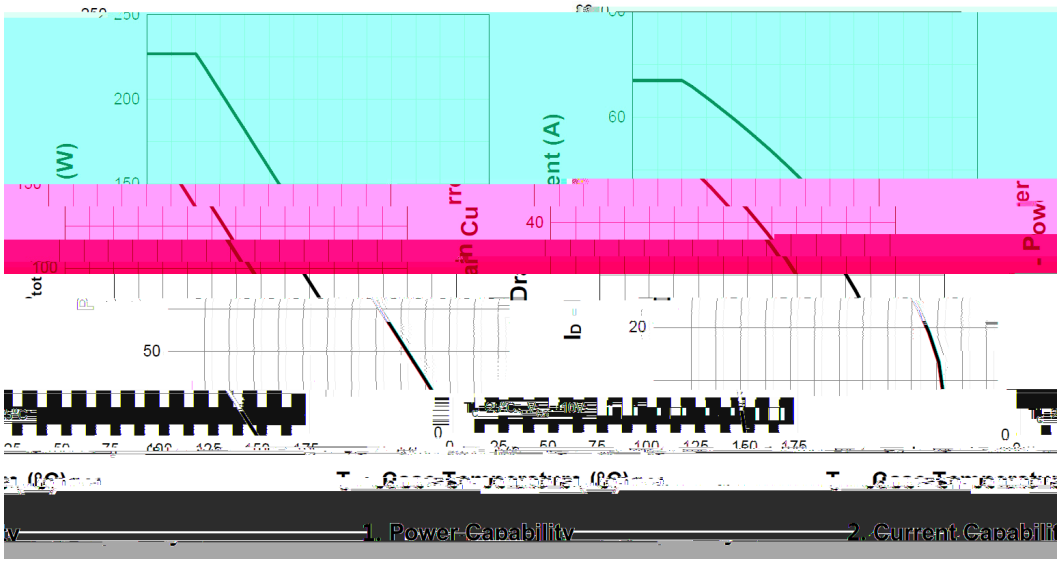
No y
* Pu Wi 300 s, Du Cy 2 %
** Su mo on 1 in 2 pa at 10 se

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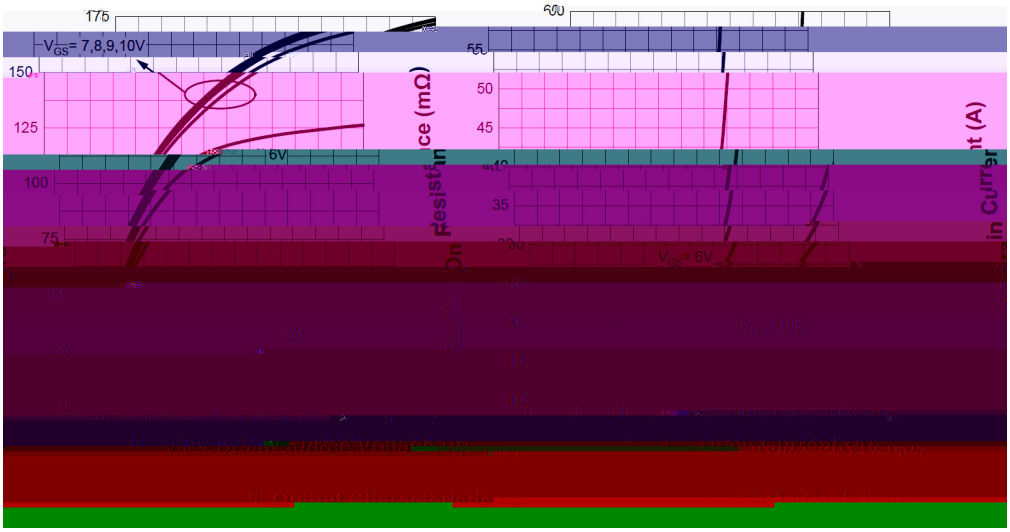
@	Z	y ¡ Ú^	´ 4	` "	´ Ý	% y
Dr So Br Vo BV	DS	VGS=0V ID=250 A	200			V
Dr Cu Cr	DS	VDS=160V VGS=0V			1	A
Ga Cu Cr	GS	VGS=f20V VDS=0V			f 100	nA
Ga Th Vo	GS(th)	VDS=VGS ID=250 A	2		4	V
St Dr So On Re	RDS(on)	VGS=10V ID=30A		17	20	m
	RDS(on)	VGS=6V ID=20A		19	22	
Fo Vo	VSD	VGS=0V IS=30A			1.3	V
Bo Ti	trr	IDS = 30 A, VGS = 0 V dISD/dt= 100 A/ s		118		ns
Bo Ch	Qrr			441		nC
In Ca	Ciss	VDS=100V VGS=0V f=1MHz		3517		pF
Ou Ca	Coss			200		
Re Ca	Crss			30		
To Ga Ch	Qg	VDS=100V VGS=10V ID=30A		59		nC
Ga So Ch	Qgs			20		
Ga Dr Ch	Qgd			14		

	t			16		
	t	r	V_{GEN}=10V V_{DS}=100V R_L=3.3 R_G=3.9 I_{DS}=30A	82		
	t			38		
	t	f		86		

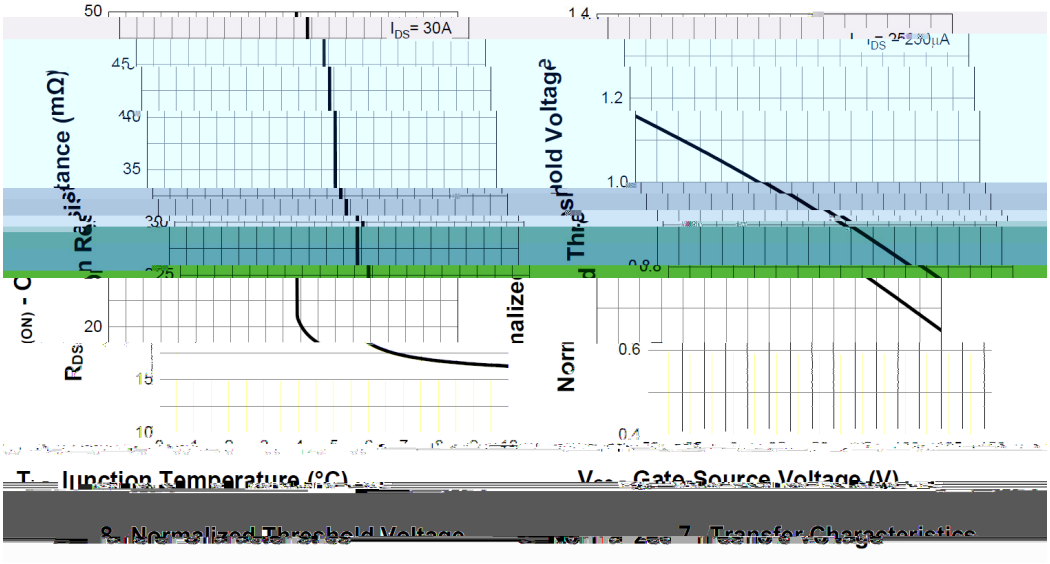
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200
(W)
60
40
50
20
0
1. Power Capability
2. Current Capabili

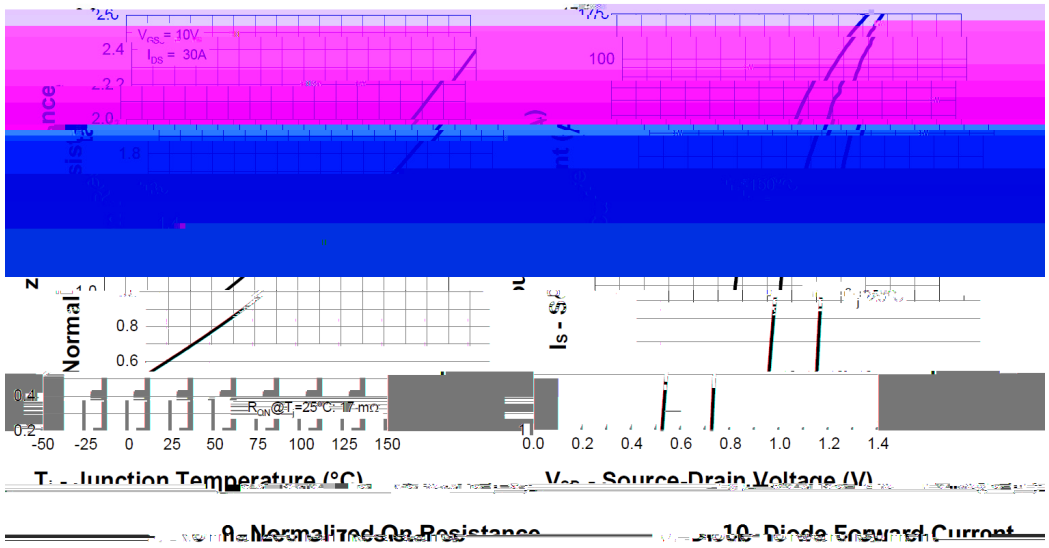

500
2
1
0.5
1ms
10ms


175
V_{GS}= 7,8,9,10V
150
125
6V
100
75
60
55
50
45
40
35
V_{DS} = 6V
(mΩ)
(A)

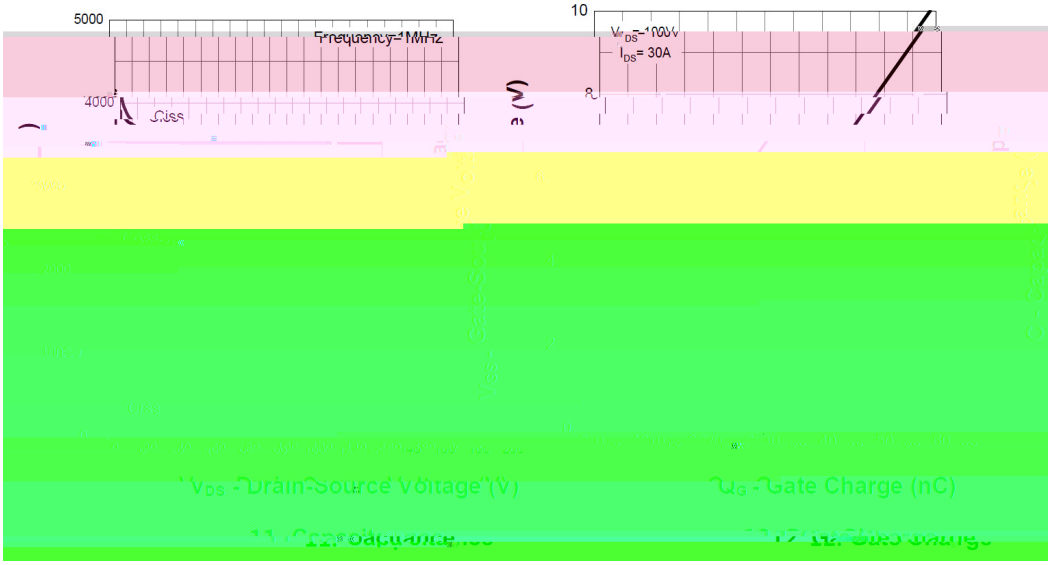
Typical Characteristics



8、Normalized Threshold Voltage　　7、Transfer Characteristics



9、Normalized On Resistance　　10、Diode Forward Current



11、Capacitance　　12、Gate Charge

Package Outline Dimensions

